

72. A single crystal GaN substrate grown on a gallium arsenide substrate followed by etching of the gallium arsenide to yield the GaN single crystal substrate free of defects caused by thermal coefficient of expansion differences.

73. The GaN single crystal substrate of claim 72, wherein the GaN single crystal substrate is of three dimensional (x,y,z) character wherein each of the dimensions x, y is at least 100 micrometers and the dimension z is at least 1 micrometer.

74. The GaN single crystal substrate of claim 72, having a thickness of from 1 to 1,000 micrometers.

75. A device structure including a device fabricated on a GaN single crystal substrate as in claim 72.


76. The device structure of claim 75, wherein the device is selected from the group consisting of LEDs, lasers, detectors, and transistors, and device precursor structures thereof.

REMARKS

The claims added and now pending in this continuation application are claims 39-76 set out above.

Concurrently submitted herewith is a petition for three months extension of time in parent Application No. 08/955,168.

Respectfully submitted,


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